

Technical documentation





TEXAS INSTRUMENTS

CD54HC85, CD74HC85, CD54HCT85, CD74HCT85 SCHS136F – AUGUST 1997 – REVISED FEBRUARY 2022

# CDx4HC85, CDx4HCT85 High-Speed CMOS Logic 4-Bit Magnitude Comparator

### **1** Features

- · Buffered inputs and outputs
- Typical propagation delay: 13 ns (data to output at  $V_{CC} = 5 \text{ V}, \text{ C}_{L} = 15 \text{ pF}, \text{ T}_{A} = 25^{\circ}\text{C}$ )
- · Serial or parallel expansion without external gating
- Fanout (over temperature range)
  - Standard outputs: 10 LSTTL loads
  - Bus driver outputs: 15 LSTTL loads
- Wide operating temperature range: –55°C to 125°C
- Balanced propagation delay and transition times
- Significant power reduction compared to LSTTL Logic ICs
- HC types
  - 2 V to 6 V operation
  - High noise immunity: N<sub>IL</sub> = 30%, N<sub>IH</sub> = 30% of V<sub>CC</sub> at V<sub>CC</sub> = 5 V
- HCT types
  - 4.5 V to 5.5 V operation
  - Direct LSTTL input logic compatibility,
  - V<sub>IL</sub> = 0.8 V (max), V<sub>IH</sub> = 2 V (min)
  - CMOS input compatibility, I<sub>I</sub>  $\leq$  1 µA at V<sub>OL</sub>, V<sub>OH</sub>

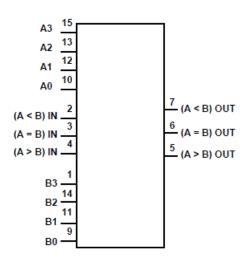
### 2 Description

The 'HC85 and 'HCT85 are high speed magnitude comparators that use silicon-gate CMOS technology to achieve operating speeds similar to LSTTL with the low power consumption of standard CMOS integrated circuits.

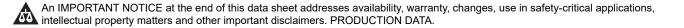
These 4-bit devices compare two binary, BCD, or other monotonic codes and present the three possible magnitude results at the outputs (A > B, A < B, and A = B). The 4-bit input words are weighted (A0 to A3 and B0 to B3), where A3 and B3 are the most significant bits.

#### **Device Information** PACKAGE **BODY SIZE (NOM)** PART NUMBER CD54HC85F3A CDIP (16) 24.38 mm × 6.92 mm CDIP (16) CD54HCT85F3A 24.38 mm × 6.92 mm CD74HC85M SOIC (16) 9.90 mm × 3.90 mm CD74HCT85M SOIC (16) 9.90 mm × 3.90 mm CD74HC85E PDIP (16) 19.31 mm × 6.35 mm CD74HCT85E PDIP (16) 19.31 mm × 6.35 mm CD74HC85NS SO (16) 6.20 mm × 5.30 mm CD74HC85PW TSSOP (16) 5.00 mm × 4.40 mm

(1) For all available packages, see the orderable addendum at the end of the data sheet.



**Functional Diagram** 





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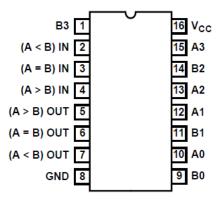
### **3 Revision History**

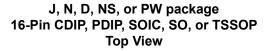
NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

С	hanges from Revision E (October 2003) to Revision F (February 2022)	Page
•	Updated the numbering, formatting, tables, figures, and cross-references throughout the document to re	flect
	modern data sheet standards	1



### **4** Pin Configuration and Functions







### **5** Specifications

#### 5.1 Absolute Maximum Ratings<sup>(1)</sup>

			MIN	MAX	UNIT
V <sub>cc</sub>	Supply voltage		-0.5	7	V
I <sub>IK</sub>	Input diode current	For V <sub>I</sub> < $-0.5$ V or V <sub>I</sub> > V <sub>CC</sub> + 0.5 V		±20	mA
I <sub>ОК</sub>	Output diode current	For V <sub>O</sub> < $-0.5$ V or V <sub>O</sub> > V <sub>CC</sub> + 0.5 V		±20	mA
lo	Output source or sink current per output pin	For $V_{O}$ > -0.5 V or $V_{O}$ < $V_{CC}$ + 0.5 V		±25	mA
I <sub>CC</sub>	Continuous current through $V_{CC}$ or GND			±50	mA
TJ	Junction temperature			150	°C
T <sub>stg</sub>	Storage temperature range		-65	150	°C
	Lead temperature (Soldering 10s) (SOIC - lead	tips only)		300	°C

(1) Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

#### **5.2 Recommended Operating Conditions**

			MIN	MAX	UNIT
V	Supply voltage range	HC types	2	6	V
V <sub>cc</sub>	Supply voltage range	HCT types	4.5	5.5	v
V <sub>I</sub> , V <sub>O</sub>	Input or output voltage		0	V <sub>CC</sub>	V
	Input rise and fall time	2 V		1000	
		4.5 V		500	ns
		6 V		400	
T <sub>A</sub>	Temperature range		-55	125	C°

#### **5.3 Thermal Information**

		D (SOIC)	N (PDIP)	NS (SO)	PW (TSSOP)	
THERM	AL METRIC	16 PINS	16 PINS	16 PINS	16 PINS	UNIT
R <sub>θJA</sub>	Junction-to-ambient thermal resistance <sup>(1)</sup>	73	67	64	108	°C/W

(1) For more information about traditional and new thermal metrics, see the Semiconductor and IC package thermal metrics application report.



#### **5.4 Electrical Characteristics**

	PARAMETER	TEST	V 00		25℃		–40°C to	85℃	–55°C to 125°C		UNIT
	PARAMETER	CONDITIONS <sup>(1)</sup>	V <sub>CC</sub> (V)	MIN	TYP	MAX	MIN	MAX	MIN	MAX	UNIT
НС ТҮ	PES										
			2	1.5			1.5		1.5		
VIH	High level input voltage		4.5	3.15			3.15		3.15		V
	. en ago		6	4.2			4.2		4.2		
			2			0.5		0.5		0.5	
VIL	Low level input voltage		4.5			1.35		1.35		1.35	V
	vollage		6			1.8		1.8		1.8	
	I Bala I and a strengt	I <sub>OH</sub> = – 20 μA	2	1.9			1.9		1.9		
	High level output voltage	Ι <sub>ΟΗ</sub> = – 20 μΑ	4.5	4.4			4.4		4.4		
V <sub>ОН</sub>	voltage	Ι <sub>ΟΗ</sub> = – 20 μΑ	6	5.9			5.9		5.9		V
	High level output	I <sub>OH</sub> = – 4 mA	4.5	3.98			3.84		3.7		
	voltage	I <sub>OH</sub> = – 5.2 mA	6	5.48			5.34		5.2		
		I <sub>OL</sub> = 20 μA	2			0.1		0.1		0.1	
	Low level output	I <sub>OL</sub> = 20 μA	4.5			0.1		0.1		0.1	V
V <sub>OL</sub>	voltage	I <sub>OL</sub> = 20 μA	6			0.1		0.1		0.1	V
	Low level output	I <sub>OL</sub> = 4 mA	4.5			0.26		0.33		0.4	
	voltage	I <sub>OL</sub> = 5.2 mA	6			0.26		0.33		0.4	V
I <sub>I</sub>	Input leakage current		6			±0.1		±1		±1	μΑ
I <sub>CC</sub>	Supply current	V <sub>I</sub> = V <sub>CC</sub> or GND	6			8		80		160	μA
нст т	YPES		1								
V <sub>IH</sub>	High level input voltage		4.5 to 5.5	2			2		2		V
V <sub>IL</sub>	Low level input voltage		4.5 to 5.5			0.8		0.8		0.8	V
V <sub>OH</sub>	High level output voltage	I <sub>OH</sub> = – 20 μA	4.5	4.4			4.4		4.4		V
∙он	High level output voltage	Ι <sub>ΟΗ</sub> = – 4 μΑ	4.5	3.98			3.84		3.7		v
	Low level output voltage	I <sub>OL</sub> = 20 μΑ	4.5			0.1		0.1		0.1	
V <sub>OL</sub>	Low level output voltage	I <sub>OL</sub> = 4 μΑ	4.5			0.26		0.33		0.4	V
lı	Input leakage current	$V_{I} = V_{CC}$ or GND	5.5			±0.1		±1		±1	μA
сс	Supply current	V <sub>I</sub> = V <sub>CC</sub> or GND	5.5			8		80		160	μA
Δl <sub>cc</sub>	Additional supply	$A_0 - A_3, B_0 - B_3$ and (A = B) IN <sup>(3)</sup>	4.5 to 5.5		100	540		675		735	μA
(2)	current per input pin	(A > B) IN, (A < B) IN <sup>(3)</sup>	4.5 to 5.5		100	360		450		490	μA

V<sub>I</sub> = V<sub>IH</sub> or V<sub>IL</sub>, unless otherwise noted.
 For dual-supply systems theoretical worst case (V<sub>I</sub> = 2.4 V, V<sub>CC</sub> = 5.5 V) specification is 1.8 mA.
 Inputs held at V<sub>CC</sub> - 2.1.



### 5.5 Switching Specifications

Input t<sub>r</sub>, t<sub>f</sub> = 6 ns

	PARAMETER			25℃		–40°C to 85°C	–55°C to 125°C	UNIT
	FARAMETER	V <sub>cc</sub> (V)	MIN	TYP	MAX	MIN MAX	MIN MAX	UNIT
НС ТҮРЕ	S							
	Propagation delay,	2			195	245	295	
t <sub>PLH</sub> , t <sub>PHL</sub>	$A_n$ , $B_n$ to (A > B) OUT,	4.5		16 <sup>(3)</sup>	39	47	59	ns
	(A < B) OUT	6			33	42	50	
		2			175	240	265	
t <sub>PLH</sub> , t <sub>PHL</sub>	$A_n$ , $B_n$ to (A = B) OUT	4.5		14 <sup>(3)</sup>	35	44	53	ns
		6			30	37	45	
		2			140	175	210	
t <sub>PLH</sub> , t <sub>PHL</sub>	(A > B) IN, $(A < B)$ IN, $(A = B)$ IN to $(A > B)$ OUT, $(A < B)$ OUT	4.5		11 <sup>(3)</sup>	28	35	42	ns
		6			24	30	36	
		2			120	150	180	
t <sub>PLH</sub> , t <sub>PHL</sub>	(A > B) IN to $(A = B)$ OUT	4.5		9 <sup>(3)</sup>	24	30	36	ns
		6			20	26	31	
C <sub>PD</sub>	Power dissipation capacitance <sup>(1) (2)</sup>	5		24				pF
		2			75	95	110	
t <sub>TLH</sub> , t <sub>THL</sub>	Output transition times (Figure 6-1)	4.5			15	19	22	ns
		6			13	16	19	
C <sub>IN</sub>	Input capacitance				10	10	10	pF
НСТ ТҮР	ES				I			
t <sub>PLH</sub> , t <sub>PHL</sub>	Propagation delay, A <sub>n</sub> , B <sub>n</sub> to (A > B) OUT, (A < B) OUT	4.5		15 <sup>(3)</sup>	37	46	56	ns
t <sub>PLH</sub> , t <sub>PHL</sub>	$A_n$ , $B_n$ to (A = B) OUT	4.5		17 <sup>(3)</sup>	40	50	60	ns
t <sub>PLH</sub> t <sub>PHL</sub>	(A > B) IN $(A < B)$ IN $(A = B)$ IN			12 <sup>(3)</sup>	30	38	45	ns
t <sub>PLH</sub> , t <sub>PHL</sub>	(A > B) IN to $(A = B)$ OUT	4.5		13 <sup>(3)</sup>	31	39	47	ns
t <sub>TLH</sub> , t <sub>THL</sub>	Output transition times (Figure 6-1)	4.5			15	19	22	ns
C <sub>PD</sub>	Power dissipation capacitance <sup>(1) (2)</sup>	5		26				pF
C <sub>IN</sub>	Input capacitance				10	10	10	pF

(1)  $C_{PD}$  is used to determine the dynamic power consumption, per gate/package. (2)  $P_D = V_{CC}^2 f_i (C_{PD} + C_L)$  where  $f_i$  = input frequency,  $C_L$  = output load capacitance,  $V_{CC}$  = supply voltage. (3)  $C_L$  = 15 pF and  $V_{CC}$  = 5 V.



### **6** Parameter Measurement Information

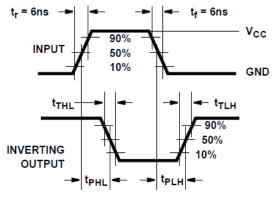


Figure 6-1. HC and HCU Transition Times and Propagation Delay Times, Combination Logic

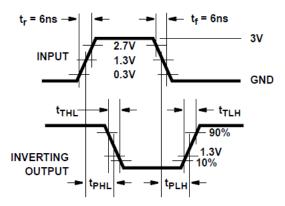
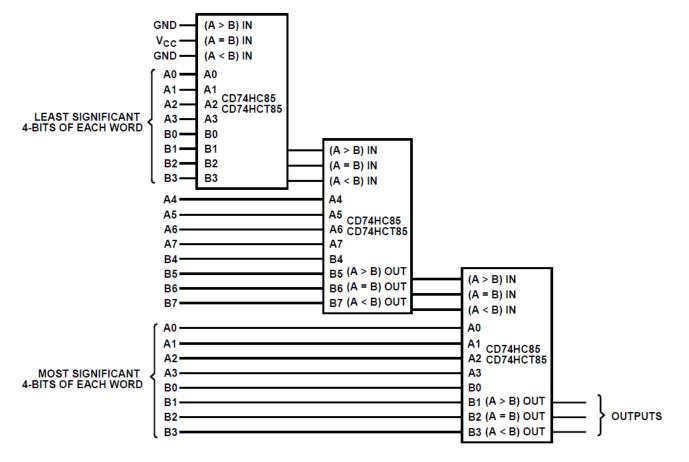
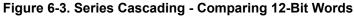


Figure 6-2. HCT Transition Times and Propagation Delay Times, Combination Logic





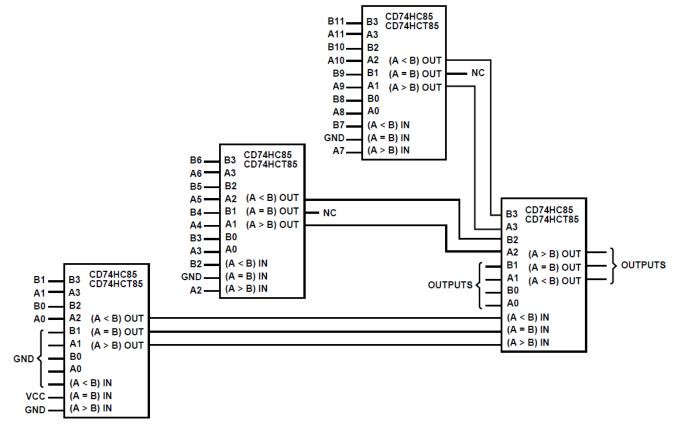


Figure 6-4. Parallel Cascading - Comparing 12-Bit Words



### 7 Detailed Description

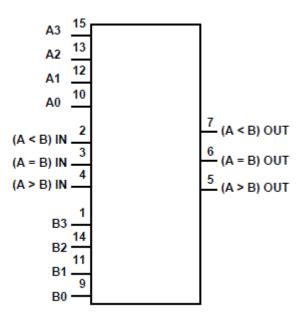
### 7.1 Overview

The 'HC85 and 'HCT85 are high speed magnitude comparators that use silicon-gate CMOS technology to achieve operating speeds similar to LSTTL with the low power consumption of standard CMOS integrated circuits.

These 4-bit devices compare two binary, BCD, or other monotonic codes and present the three possible magnitude results at the outputs (A > B, A < B, and A = B). The 4-bit input words are weighted (A0 to A3 and B0 to B3), where A3 and B3 are the most significant bits.

The devices are expandable without external gating, in both serial and parallel fashion. The upper part of the truth table indicates operation using a single device or devices in a serially expanded application. The parallel expansion scheme is described by the last three entries in the truth table.

#### 7.2 Functional Block Diagram





### 7.3 Device Functional Modes

			Т	able 7-1. T	ruth Table <sup>(</sup>	1)				
	COMPARIN	NG INPUTS		CA	SCADING INP	UTS	OUTPUTS			
A3, B3	A2, B2	A1, B1	A0, B0	A > B	A < B	A = B	A > B	A < B	A = B	
SINGLE DEV	ICE OR SERI	ES CASCADI	NG							
A3 > B3	Х	Х	Х	Х	Х	Х	Н	L	L	
A3 < B3	Х	Х	Х	Х	Х	Х	L	Н	L	
A3 = B3	A2 >B2	Х	Х	Х	Х	Х	Н	L	L	
A3 = B3	A2 < B2	Х	Х	Х	Х	Х	L	н	L	
A3 = B3	A2 = B2	A1 > B1	Х	Х	Х	Х	Н	L	L	
A3 = B3	A2 = B2	A1 < B1	Х	Х	Х	Х	L	Н	L	
A3 = B3	A2 = B2	A1 = B1	A0 > B0	Х	Х	Х	Н	L	L	
A3 = B3	A2 = B2	A1 = B1	A0 < B0	Х	Х	Х	L	Н	L	
A3 = B3	A2 = B2	A1 = B1	A0 = B0	Н	L	L	н	L	L	
A3 = B3	A2 = B2	A1 = B1	A0 = B0	L	н	L	L	Н	L	
A3 = B3	A2 = B2	A1 = B1	A0 = B0	L	L	Н	L	L	Н	
PARALLEL	CASCADING	1	11		1	1	•			
A3 = B3	A2 = B2	A1 = B1	A0 = B0	Х	Х	Н	L	L	Н	
A3 = B3	A2 = B2	A1 = B1	A0 = B0	Н	Н	L	L	L	L	
A3 = B3	A2 = B2	A1 = B1	A0 = B0	L	L	L	н	Н	L	

(1) H = high voltage level, L = low voltage level, X = don't care



### 8 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating located in the *Recommended Operating Conditions*. Each  $V_{CC}$  terminal should have a good bypass capacitor to prevent power disturbance. A 0.1- $\mu$ F capacitor is recommended for this device. It is acceptable to parallel multiple bypass caps to reject different frequencies of noise. The 0.1- $\mu$ F and 1- $\mu$ F capacitors are commonly used in parallel. The bypass capacitor should be installed as close to the power terminal as possible for best results.

### 9 Layout

#### 9.1 Layout Guidelines

When using multiple-input and multiple-channel logic devices inputs must not ever be left floating. In many cases, functions or parts of functions of digital logic devices are unused; for example, when only two inputs of a triple-input AND gate are used or only 3 of the 4 buffer gates are used. Such unused input pins must not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. All unused inputs of digital logic devices must be connected to a logic high or logic low voltage, as defined by the input voltage specifications, to prevent them from floating. The logic level that must be applied to any particular unused input depends on the function of the device. Generally, the inputs are tied to GND or  $V_{CC}$ , whichever makes more sense for the logic function or is more convenient.



### **10 Device and Documentation Support**

TI offers an extensive line of development tools. Tools and software to evaluate the performance of the device, generate code, and develop solutions are listed below.

#### **10.1 Receiving Notification of Documentation Updates**

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Subscribe to updates* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

#### **10.2 Support Resources**

TI E2E<sup>™</sup> support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

#### 10.3 Trademarks

TI E2E<sup>™</sup> is a trademark of Texas Instruments. All trademarks are the property of their respective owners.

#### **10.4 Electrostatic Discharge Caution**



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

### 10.5 Glossary

TI Glossary This glossary lists and explains terms, acronyms, and definitions.

### 11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.



### PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
5962-8867201EA	ACTIVE	CDIP	J	16	1	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	5962-8867201EA CD54HCT85F3A	Samples
8601301EA	ACTIVE	CDIP	J	16	1	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	8601301EA CD54HC85F3A	Samples
CD54HC85F3A	ACTIVE	CDIP	J	16	1	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	8601301EA CD54HC85F3A	Samples
CD54HCT85F3A	ACTIVE	CDIP	J	16	1	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	5962-8867201EA CD54HCT85F3A	Samples
CD74HC85E	ACTIVE	PDIP	Ν	16	25	RoHS & Green	NIPDAU	N / A for Pkg Type	-55 to 125	CD74HC85E	Samples
CD74HC85EE4	ACTIVE	PDIP	N	16	25	RoHS & Green	NIPDAU	N / A for Pkg Type	-55 to 125	CD74HC85E	Samples
CD74HC85M96	ACTIVE	SOIC	D	16	2500	RoHS & Green	NIPDAU   SN	Level-1-260C-UNLIM	-55 to 125	HC85M	Samples
CD74HC85NSR	ACTIVE	SO	NS	16	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-55 to 125	HC85M	Samples
CD74HC85PWR	ACTIVE	TSSOP	PW	16	2000	RoHS & Green	NIPDAU   SN	Level-1-260C-UNLIM	-55 to 125	HJ85	Samples
CD74HCT85E	ACTIVE	PDIP	N	16	25	RoHS & Green	NIPDAU	N / A for Pkg Type	-55 to 125	CD74HCT85E	Samples
CD74HCT85M	ACTIVE	SOIC	D	16	40	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-55 to 125	HCT85M	Samples
CD74HCT85MT	ACTIVE	SOIC	D	16	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-55 to 125	HCT85M	Samples

<sup>(1)</sup> The marketing status values are defined as follows: **ACTIVE:** Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.



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# PACKAGE OPTION ADDENDUM

<sup>(3)</sup> MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

<sup>(4)</sup> There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

**Important Information and Disclaimer:**The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

#### OTHER QUALIFIED VERSIONS OF CD54HC85, CD54HCT85, CD74HC85, CD74HCT85 :

• Catalog : CD74HC85, CD74HCT85

• Military : CD54HC85, CD54HCT85

NOTE: Qualified Version Definitions:

- Catalog TI's standard catalog product
- Military QML certified for Military and Defense Applications



Texas

STRUMENTS

### TAPE AND REEL INFORMATION





#### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal												
Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CD74HC85M96	SOIC	D	16	2500	330.0	16.4	6.5	10.3	2.1	8.0	16.0	Q1
CD74HC85M96	SOIC	D	16	2500	330.0	16.4	6.6	9.3	2.1	8.0	16.0	Q1
CD74HC85NSR	SO	NS	16	2000	330.0	16.4	8.2	10.5	2.5	12.0	16.0	Q1
CD74HC85NSR	SO	NS	16	2000	330.0	16.4	8.2	10.5	2.5	12.0	16.0	Q1
CD74HC85PWR	TSSOP	PW	16	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
CD74HC85PWR	TSSOP	PW	16	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
CD74HC85PWR	TSSOP	PW	16	2000	330.0	12.4	6.85	5.45	1.6	8.0	12.0	Q1



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# PACKAGE MATERIALS INFORMATION

12-Oct-2023



Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
CD74HC85M96	SOIC	D	16	2500	356.0	356.0	35.0
CD74HC85M96	SOIC	D	16	2500	366.0	364.0	50.0
CD74HC85NSR	SO	NS	16	2000	356.0	356.0	35.0
CD74HC85NSR	SO	NS	16	2000	367.0	367.0	38.0
CD74HC85PWR	TSSOP	PW	16	2000	356.0	356.0	35.0
CD74HC85PWR	TSSOP	PW	16	2000	356.0	356.0	35.0
CD74HC85PWR	TSSOP	PW	16	2000	366.0	364.0	50.0

### TEXAS INSTRUMENTS

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### TUBE



### - B - Alignment groove width

#### \*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	Τ (μm)	B (mm)
CD74HC85E	N	PDIP	16	25	506	13.97	11230	4.32
CD74HC85E	N	PDIP	16	25	506	13.97	11230	4.32
CD74HC85EE4	N	PDIP	16	25	506	13.97	11230	4.32
CD74HC85EE4	N	PDIP	16	25	506	13.97	11230	4.32
CD74HCT85E	N	PDIP	16	25	506	13.97	11230	4.32
CD74HCT85E	N	PDIP	16	25	506	13.97	11230	4.32
CD74HCT85M	D	SOIC	16	40	507	8	3940	4.32

# **NS0016A**



# **PACKAGE OUTLINE**

SOP - 2.00 mm max height

SOP



#### NOTES:

- 1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing
- Per ASME Y14.5M.
  This drawing is subject to change without notice.
  This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm, per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm, per side.



# NS0016A

# **EXAMPLE BOARD LAYOUT**

### SOP - 2.00 mm max height

SOP



NOTES: (continued)

5. Publication IPC-7351 may have alternate designs.

6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



# NS0016A

# **EXAMPLE STENCIL DESIGN**

## SOP - 2.00 mm max height

SOP



NOTES: (continued)

7. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

8. Board assembly site may have different recommendations for stencil design.



D (R-PDSO-G16)

PLASTIC SMALL OUTLINE



NOTES: A. All linear dimensions are in inches (millimeters).

- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
- E. Reference JEDEC MS-012 variation AC.



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# D (R-PDSO-G16) PLASTIC SMALL OUTLINE Stencil Openings (Note D) Example Board Layout (Note C) –16x0,55 -14x1,27 -14x1,27 16x1,50 5,40 5.40 Example Non Soldermask Defined Pad Example Pad Geometry (See Note C) 0,60 .55 Example 1. Solder Mask Opening (See Note E) -0,07 All Around

NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
  E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



# **PW0016A**



# **PACKAGE OUTLINE**

# TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M. 2. This drawing is subject to change without notice. 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-153.



# PW0016A

# **EXAMPLE BOARD LAYOUT**

# TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



# PW0016A

# **EXAMPLE STENCIL DESIGN**

# TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



NOTES: (continued)

9. Board assembly site may have different recommendations for stencil design.



<sup>8.</sup> Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

### MECHANICAL DATA

### PLASTIC SMALL-OUTLINE PACKAGE

#### 0,51 0,35 ⊕0,25⊛ 1,27 8 14 0,15 NOM 5,60 8,20 5,00 7,40 $\bigcirc$ Gage Plane ₽ 0,25 7 1 1,05 0,55 0-10 Δ 0,15 0,05 Seating Plane — 2,00 MAX 0,10PINS \*\* 14 16 20 24 DIM 10,50 10,50 12,90 15,30 A MAX A MIN 9,90 9,90 12,30 14,70 4040062/C 03/03

NOTES: A. All linear dimensions are in millimeters.

NS (R-PDSO-G\*\*)

**14-PINS SHOWN** 

- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion, not to exceed 0,15.



J (R-GDIP-T\*\*) 14 LEADS SHOWN

CERAMIC DUAL IN-LINE PACKAGE



NOTES: A. All linear dimensions are in inches (millimeters).

- B. This drawing is subject to change without notice.
- C. This package is hermetically sealed with a ceramic lid using glass frit.
- D. Index point is provided on cap for terminal identification only on press ceramic glass frit seal only.
- E. Falls within MIL STD 1835 GDIP1-T14, GDIP1-T16, GDIP1-T18 and GDIP1-T20.

# N (R-PDIP-T\*\*)

PLASTIC DUAL-IN-LINE PACKAGE

16 PINS SHOWN



NOTES:

- A. All linear dimensions are in inches (millimeters).B. This drawing is subject to change without notice.
- Falls within JEDEC MS-001, except 18 and 20 pin minimum body length (Dim A).
- $\triangle$  The 20 pin end lead shoulder width is a vendor option, either half or full width.



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